

ABSTRACT

The present invention is provided to form a trench in a semiconductor device, wherein by performing an ion implanting process to an area of a semiconductor substrate in which the trench would be formed to cause lattice 5 defects in the area before forming the trench, an etching speed of the area is increased in subsequent trench forming processes. As a result, it is possible to prevent micro trenches from being formed in edge portions of patterns and to suppress a micro loading effect to be generated depending upon pattern sizes.